NPN High-Power Transistors

Designed for general-purpose power amplifier and switching applications.

Features

• ESD Ratings: Machine Model, C; > 400 V Human Body Model, 3B; > 8000 V

• Epoxy Meets UL 94 V-0 @ 0.125 in

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector – Emitter Voltage	TIP33A TIP33C	V _{CEO}	60 100	Vdc
Collector – Base Voltage	TIP33A TIP33C	V _{CBO}	60 100	Vdc
Emitter – Base Voltage		V _{EBO}	5.0	Vdc
Collector Current – Continuous – Peak (Note 1)		I _C	10 15	Adc Apk
Base Current – Continuous		I _B	3.0	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C		P _D	80 0.64	Watts W/°C
Operating and Storage Junction Temperature Range		T _J , T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.56	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	35.7	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

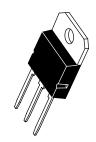
1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.



ON Semiconductor®

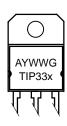
http://onsemi.com

10 AMPERE NPN SILICON POWER TRANSISTORS 60 & 100 VOLT, 80 WATTS



SOT-93 (TO-218) CASE 340D STYLE 1

MARKING DIAGRAM



A = Assembly Location

= Year

WW = Work Week
TIP33x = Device Code
x = A or C

G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
TIP33A	TO-218	30 Units / Rail
TIP33AG	TO-218 (Pb-Free)	30 Units / Rail
TIP33C	TO-218	30 Units / Rail
TIP33CG	TO-218 (Pb-Free)	30 Units / Rail

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u>.</u>				
Collector–Emitter Sustaining Voltage (Note 2) (I _C = 30 mA, I _B = 0)	TIP33A TIP33C	V _{CEO(sus)}	60 100	_ _	Vdc
Collector–Emitter Cutoff Current $(V_{CE} = 30 \text{ V}, I_B = 0)$ $(V_{CE} = 60 \text{ V}, I_B = 0)$	TIP33A TIP33C	I _{CEO}	_	0.7	mA
Collector–Emitter Cutoff Current $(V_{CE} = Rated V_{CEO}, V_{EB} = 0)$		I _{CES}	_	0.4	mA
Emitter–Base Cutoff Current $(V_{EB} = 5.0 \text{ V}, I_{C} = 0)$		I _{EBO}	_	1.0	mA
ON CHARACTERISTICS (Note 2)					
DC Current Gain (I _C = 1.0 A, V _{CE} = 4.0 V) (I _C = 3.0 A, V _{CE} = 4.0 V)		h _{FE}	40 20	_ 100	_
Collector–Emitter Saturation Voltage ($I_C = 3.0 \text{ A}, I_B = 0.3 \text{ A}$) ($I_C = 10 \text{ A}, I_B = 2.5 \text{ A}$)		V _{CE(sat)}	_ _	1.0 4.0	Vdc
Base–Emitter On Voltage (I _C = 3.0 A, V _{CE} = 4.0 V) (I _C = 10 A, V _{CE} = 4.0 V)		V _{BE(on)}	_ _	1.6 3.0	Vdc
DYNAMIC CHARACTERISTICS			•	•	•
Small–Signal Current Gain (I _C = 0.5 A, V _{CE} = 10 V, f = 1.0 kHz)		h _{fe}	20	-	-
Current-Gain — Bandwidth Product (I _C = 0.5 A, V _{CE} = 10 V, f = 1.0 MHz)		fτ	3.0	-	MHz

^{2.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

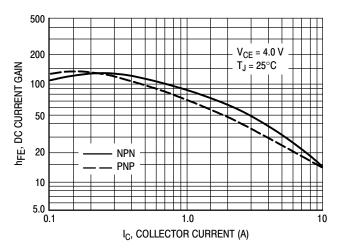


Figure 1. DC Current Gain

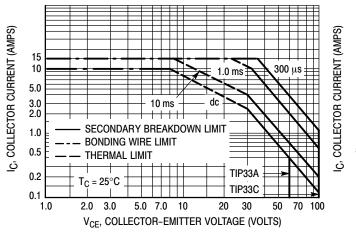


Figure 2. Maximum Rated Forward Bias Safe Operating Area

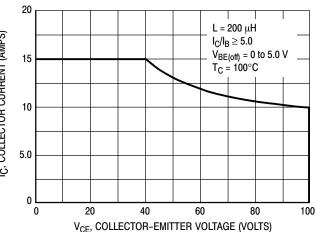


Figure 3. Maximum Rated Forward Bias Safe Operating Area

FORWARD BIAS

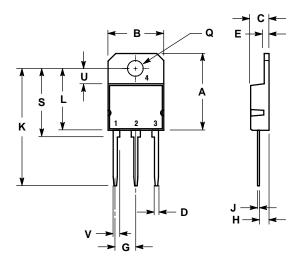
The Forward Bias Safe Operating Area represents the voltage and current conditions these devices can withstand during forward bias. The data is based on $T_C=25\,^{\circ}\mathrm{C};\,T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10%, and must be derated thermally for $T_C>25\,^{\circ}\mathrm{C}.$

REVERSE BIAS

The Reverse Bias Safe Operating Area represents the voltage and current conditions these devices can withstand during reverse biased turn-off. This rating is verified under clamped conditions so the device is never subjected to an avalanche mode.

PACKAGE DIMENSIONS

SOT-93 (TO-218) CASE 340D-02 **ISSUE E**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α		20.35		0.801	
В	14.70	15.20	0.579	0.598	
C	4.70	4.90	0.185	0.193	
D	1.10	1.30	0.043	0.051	
Е	1.17	1.37	0.046	0.054	
G	5.40	5.55	0.213	0.219	
Н	2.00	3.00	0.079	0.118	
J	0.50	0.78	0.020	0.031	
K	31.00	31.00 REF		1.220 REF	
L		16.20		0.638	
Q	4.00	4.10	0.158	0.161	
S	17.80	18.20	0.701	0.717	
U	4.00 REF		0.157 REF		
٧	1.75 REF		0.069		

STYLE 1:

PIN 1. BASE

- COLLECTOR
- 3 **EMITTER**
- COLLECTOR

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TIP33C/D